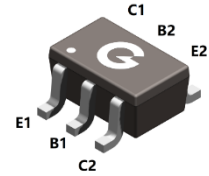
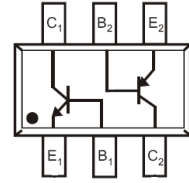


Features

- Epitaxial planar die construction
- Two internal isolated NPN/PNP transistors in one package
- Ultra-small surface mount package
- RoHS compliant with Halogen-free
- Qualified to AEC-Q101 Standards

HF



SOT-363

Mechanical Data

- Case: SOT-363
- Molding compound: UL flammability classification rating 94V-0
- Terminals: Tin-plated; solderability per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
TBC847PN	SOT-363	3000 pcs / Tape & Reel	7P

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	NPN	PNP	Unit
Collector-Base Voltage	V _{CBO}	50	-50	V
Collector-Emitter Voltage	V _{CEO}	45	-45	V
Emitter-Base Voltage	V _{EBO}	6	-5	V
Collector Current (Continuous)	I _C	100	-100	mA
Collector Current (Pulse)	I _{CM}	200	-200	mA

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation	P _D	200	mW
Thermal Resistance Junction-to-Air ^{*1}	R _{θJA}	370	°C/W
Thermal Resistance Junction-to-Case ^{*1}	R _{θJC}	250	°C/W
Thermal Resistance Junction-to-Lead ^{*1}	R _{θJL}	300	°C/W
Operating Junction Temperature	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Note 1: The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper

Electrical Characteristics of NPN Transistor (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}, I_E = 0$	50	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{mA}, I_B = 0$	45	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 1\mu\text{A}, I_C = 0$	6	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = 30\text{V}, I_E = 0$	-	-	15	nA
DC Current Gain	h_{FE}	$V_{CE} = 5\text{V}, I_C = 2\text{mA}$	200	290	450	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$	-	0.09	0.25	V
		$I_C = 100\text{mA}, I_B = 5\text{mA}$	-	0.20	0.60	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$	-	0.70	-	V
		$I_C = 100\text{mA}, I_B = 5\text{mA}$	-	0.90	-	V
Base-Emitter Voltage	$V_{BE(ON)}$	$V_{CE} = 5\text{V}, I_C = 2\text{mA}$	0.58	0.66	0.70	V
		$V_{CE} = 5\text{V}, I_C = 10\text{mA}$	-	-	0.72	V
Transition Frequency	f_T	$V_{CE} = 5\text{V}, I_C = 10\text{mA}$ $f = 100\text{MHz}$	100	-	-	MHz
Output Capacitance	C_{OBO}	$V_{CB} = 10\text{V}, f = 1.0\text{MHz}$	-	3.5	6.0	pF
Noise Figure	N_F	$V_{CE} = 5\text{V}, f = 1.0\text{MHz}$ $I_C = 200\text{mA}, R_G = 2\text{k}\Omega$	-	2.0	10	dB

Electrical Characteristics of PNP Transistor (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}, I_E = 0$	-50	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	-45	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -1\mu\text{A}, I_C = 0$	-6	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -30\text{V}, I_E = 0$	-	-	-15	nA
DC Current Gain	h_{FE}	$V_{CE} = -5\text{V}, I_C = -2\text{mA}$	200	290	450	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -10\text{mA}, I_B = -0.5\text{mA}$	-	-0.075	-0.3	V
		$I_C = -100\text{mA}, I_B = -5\text{mA}$	-	-0.25	-0.65	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -10\text{mA}, I_B = -0.5\text{mA}$	-	-0.70	-	V
		$I_C = -100\text{mA}, I_B = -5\text{mA}$	-	-0.85	-0.95	V
Base-Emitter Voltage	$V_{BE(ON)}$	$V_{CE} = -5\text{V}, I_C = -2\text{mA}$	-0.6	-0.65	-0.75	V
		$V_{CE} = -5\text{V}, I_C = -10\text{mA}$	-	-	-0.82	V
Transition Frequency	f_T	$V_{CE} = -5\text{V}, I_C = -10\text{mA}$ $f = 100\text{MHz}$	100	-	-	MHz
Output Capacitance	C_{OBO}	$V_{CB} = -10\text{V}, f = 1.0\text{MHz}$	-	3	4.5	pF
Noise Figure	N_F	$V_{CE} = -5\text{V}, f = 1.0\text{MHz}$ $I_C = -200\text{mA}, R_G = -2\text{k}\Omega$	-	-	10	dB

Ratings and Characteristic Curves - NPN (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

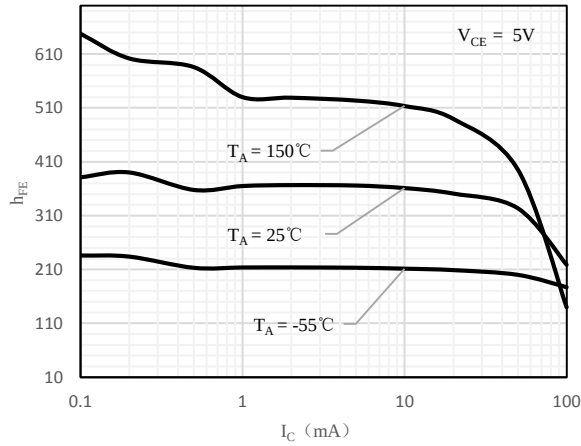


Fig 1 h_{FE} vs. I_C

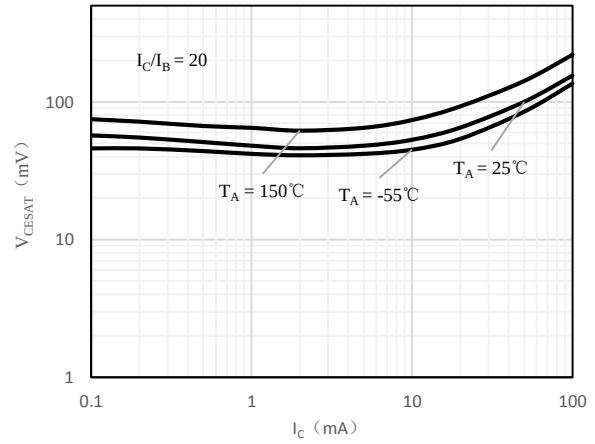


Fig 2 $V_{CE(sat)}$ vs. I_C

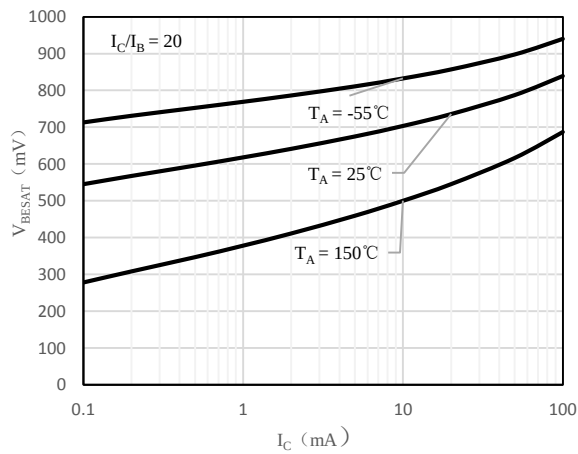


Fig 3 $V_{BE(sat)}$ vs. I_C

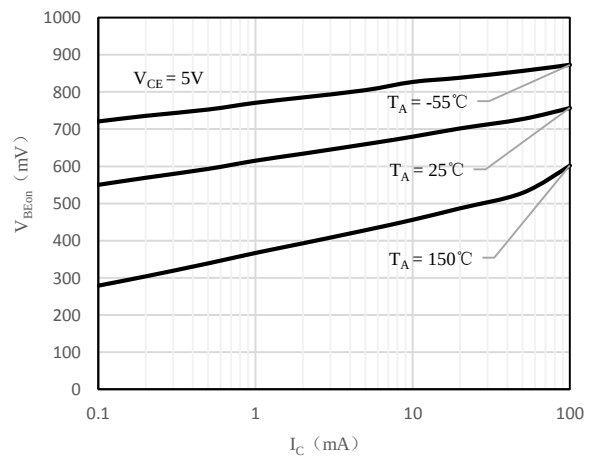


Fig 4 $V_{BE(on)}$ vs. I_C

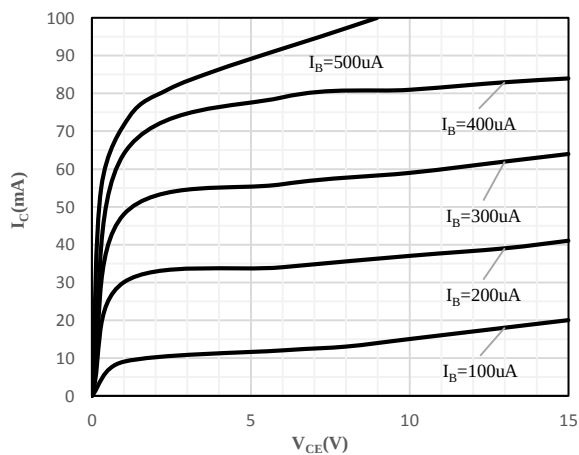


Fig 5 I_C vs. V_{CE}

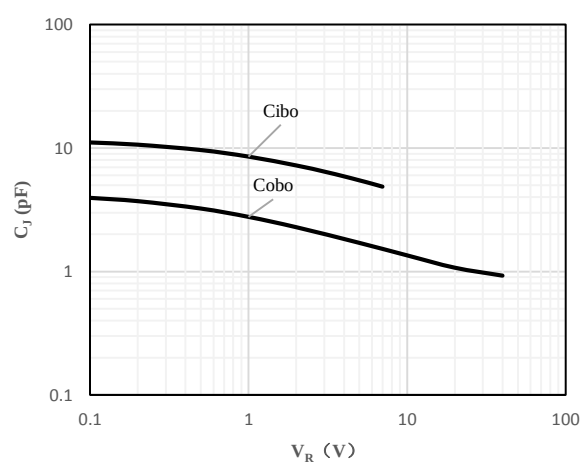


Fig 6 C_J vs. V_R

Ratings and Characteristic Curves - PNP (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

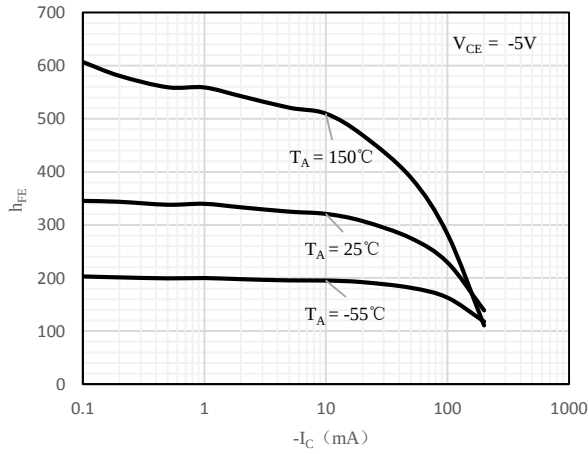


Fig 1 h_{FE} vs. I_C

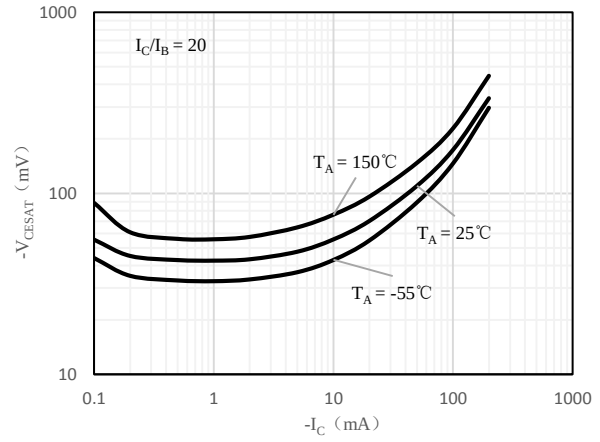


Fig 2 $V_{CE(sat)}$ vs. I_C

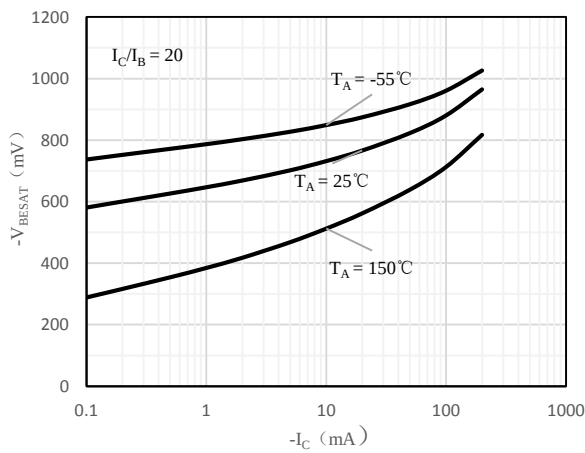


Fig 3 $V_{BE(sat)}$ vs. I_C

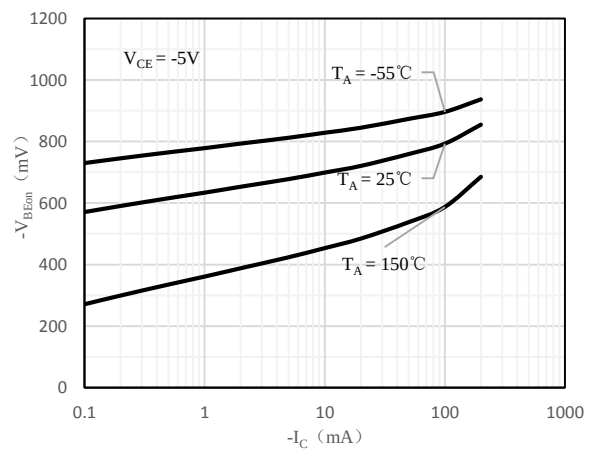


Fig 4 $V_{BE(on)}$ vs. I_C

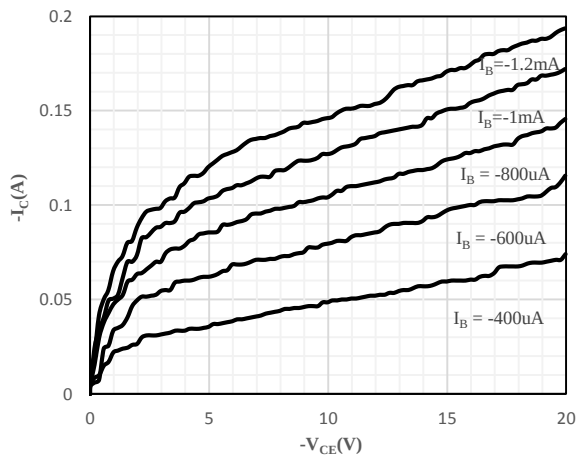


Fig 5 I_C vs. V_{CE}

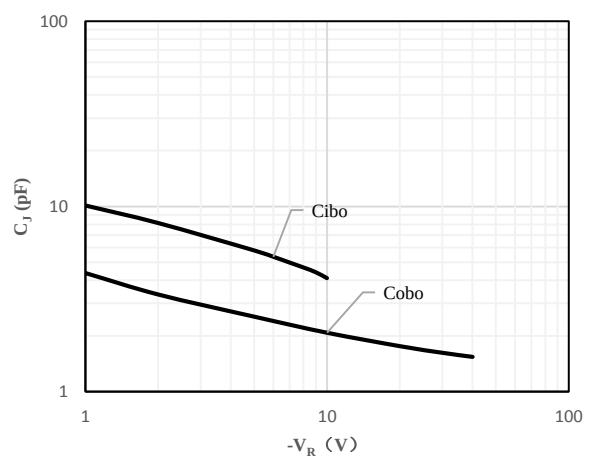
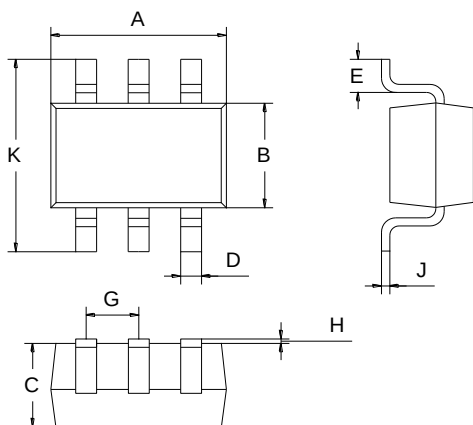


Fig 6 C_J vs. V_R

Package Outline Dimensions (Unit: mm)



SOT-363		
Dimension	Min.	Max.
A	2.00	2.20
B	1.15	1.35
C	0.85	1.05
D	0.15	0.35
E	0.25	0.40
G	0.60	0.70
H	0.02	0.10
J	0.05	0.15
K	2.20	2.40

Package Outline Dimensions (Unit: mm)

SOT-363

